CNZ2253 (ON2253)

Reflective photosensor

Non-contact point SW, object sensing

Overview

CNZ2253 is a photosensor detecting the change of reflective light in which a high efficiency GaAs infrared light emitting diode is used as the light emitting element, and a high sensitivity Si Darlington phototransistor is used as the light detecting element. The two elements are located parallel in the same direction and objects are detected when passing in front of the device.

Features

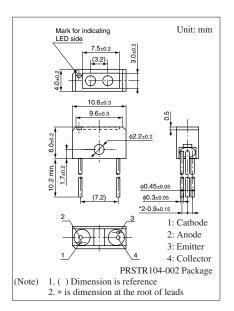
- High sensitivity
- Small size and light weight

Applications

- Detection of paper, film and cloth Optical mark reading
- Detection of coin and bill
- Detection of position and edge
- Start, end mark detection of magnetic tape

■ Absolute Maximum Ratings $T_a = 25$ °C

	Parameter	Symbol	Rating	Unit
Input (Light	Reverse voltage	V _R	3	V
emitting diode)	Forward current	I_{F}	50	mA
	Power dissipation *1	P_{D}	75	mW
Output (Photo	Collector-emitter voltage	V _{CEO}	20	V
transistor)	(Base open)			
	Emitter-collector voltage	V _{ECO}	5	V
	(Base open)			
	Collector current	I_C	30	mA
	Collector power dissipation *2	P _C	100	mW
Temperature	Operating ambient temperature	Topr	-25 to +85	°C
	Storage temperature	T _{stg}	-30 to +100	°C



Note) *1: Input power derating ratio is $1.0 \text{ mW/}^{\circ}\text{C}$ at $T_a \ge 25^{\circ}\text{C}$.

*2: Output power derating ratio is $1.34 \text{ mW/}^{\circ}\text{C}$ at $T_a \ge 25^{\circ}\text{C}$.

■ Electrical-Optical Characteristics $T_a = 25$ °C ± 3 °C

	Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Input	Forward voltage	$V_{\rm F}$	$I_F = 50 \text{ mA}$		1.2	1.5	V
characteristics	Reverse current	I_R	$V_R = 3 V$			10	μΑ
	Terminal capacitance	Ct	$V_R = 0 V, f = 1 MHz$		50		pF
Output	Collector-emitter cutoff current	I _{CEO}	$V_{CE} = 10 \text{ V}$			0.5	μΑ
characteristics	(Base open)						
Transfer	Collector current *1, 2	I_C	$V_{CC} = 5 \text{ V}, I_F = 10 \text{ mA}, R_L = 100 \Omega$	3		30	mA
characteristics	Collector-emitter saturation voltage	V _{CE(sat)}	$I_F = 50 \text{ mA}, I_C = 1 \text{ mA}$			1.5	V
	Rise time	t _r	$V_{CC} = 10 \text{ V}, I_C = 1 \text{ mA}, R_L = 100 \Omega$		150		μs
	Fall time	$t_{\rm f}$			150		μs

Note) 1. Input and output are handled electrically.

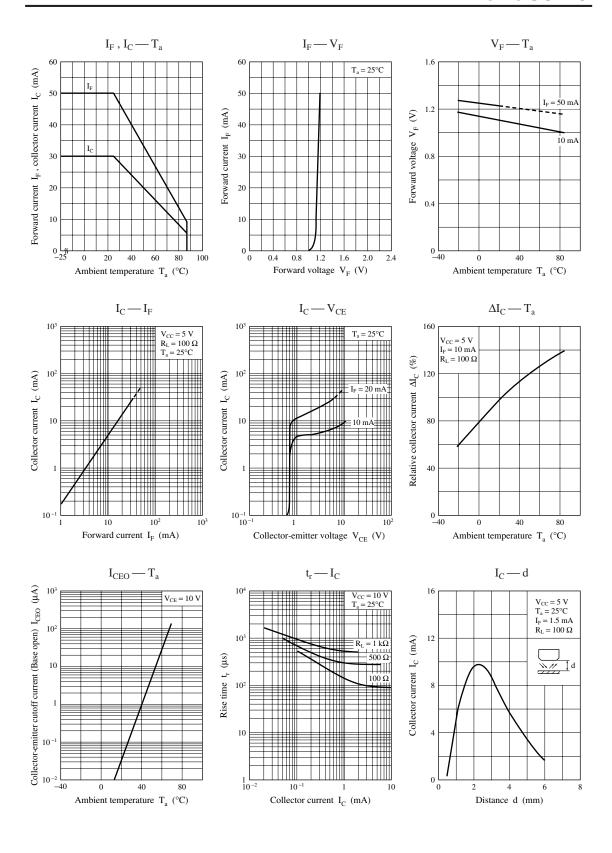
- 2. This product is not designed to withstand radiation I_F
- 3. *1: Output current measurement circuit (Ambient light is shut off completely)

*2: Rank classification

Rank	Q	R	S	No-rank
I_{C} (mA)	3 to 9	6 to 18	12 to 30	3 to 30



Note) The part number in the parenthesis shows conventional part number.



Caution for Safety

⚠ DANGER

■ This product contains Gallium Arsenide (GaAs).

GaAs powder and vapor are hazardous to human health if inhaled or ingested. Do not burn, destroy, cut, cleave off, or chemically dissolve the product. Follow related laws and ordinances for disposal. The product should be excluded form general industrial waste or household garbage.

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